

Switching diode

1SS355

● Applications

High speed switching

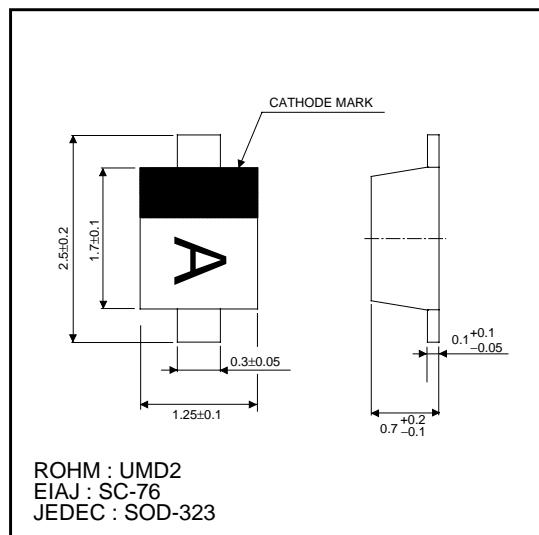
● Features

- 1) Small surface mounting type.(UMD2)
- 2) High Speed.($t_{rf}=1.2\text{ns}$ Typ.)
- 3) High reliability with high surge current handling capability.

● Construction

Silicon epitaxial planar

● External dimensions (Units : mm)



● Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	90	V
DC reverse voltage	V_R	80	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_o	100	mA
Surge current (1s)	I_{surge}	500	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~+125	$^\circ\text{C}$

● Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	-	1.2	V	$I_F=100\text{mA}$
Reverse current	I_R	-	-	0.1	μA	$V_R=80\text{V}$
Capacitance between terminals	C_T	-	-	3.0	pF	$V_R=0.5\text{V}, f=1\text{MHz}$
Reverse recovery time	t_{rr}	-	-	4	ns	$V_R=6\text{V}, I_F=10\text{mA}, R_L=100\Omega$

Diodes

● Electrical characteristic curves ($T_a=25^\circ C$)